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Detection of single electron heat transfer statistics

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We consider a quantum dot system whose charge fluctuations are monitored by a quantum point contact allowing for the detection of both charge and transferred heat statistics. Our system consists of two nearby conductors that exchange energy via Coulomb interaction. In interfaces consisting of capacitively coupled quantum dots, energy transfer is discrete. In the presence of hot spots, we predict gate dependent deviations away from a fluctuation theorem that holds for charge currents in the absence of temperature gradients. A fluctuation theorem holds for coupled dot configurations with heat exchange and no net particle flow.

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I. INTRODUCTION

Contrary to charge, heat currents are difficult to measure on nanoscopic scales[1]. Seebeck-Onsager coefficients relate heat flows to voltage drops[2] allowing for the detection of mesoscopic heat currents in the linear regime[3,4]. Recently multiterminal arrangements have been used to inject current and as thermometers in heat transistors[5]. However, a method for a direct measurement of non linear electronic heat currents and their fluctuations has not been described. It would allow for instance to investigate recent proposals of refrigerators[6,7], efficient heat converters[8–11], rectifiers[12] or diodes[13] based on single electron transistors.

Measurements of the charge counting statistics have become a standard way to access the noise properties of the electric flows through quantum dot systems[14–16]. There, time resolved charge fluctuations are detected by current changes though a capacitively coupled quantum point contact (QPC). Experimental precision makes possible to measure the behaviour of high order cumulants or finitie ferquency statistics[17,18]. For this reason, mesoscopic conductors offer an ideal playground for experimental verifications of nonlinear fluctuation relations as expressed for electric conduction[19–24]. Pioneering experiments have been carried out recently[25,26]. In experiments where the detector is asymmetrically coupled to a double quantum dot[15,26], different charge distributions are resolved as different outputs in the QPC. This way trajectories of charges flowing along and against an applied voltage can be traced out. If the external force is thermal, so temperature is inhomogeneous, the fluctuation theorem for charge currents does not hold. One must then consider both charge and energy currents[27] or, alternatively, heat. To test fluctuation relations, the ability to measure heat currents is therefore also of fundamental importance.

Here we show that charge counting statistics measurements can give access to heat flows and their fluctuations in systems of quantum dots. It allows for tests of non linear fluctuation relations for transport in the presence of thermal and voltage gradients. To illustrate this generally, we consider a model of capacitively coupled conductors that allows to separate heat and charge flows: charge flows through the terminals of each conductor; energy is exchanged via electron-electron interactions, as sketched in Fig. 1. Two quantum dots are close enough such that their charge is mutually affected by Coulomb interaction with a capacitance coupling, C. Experiments have demonstrated a strong interdot coupling with no electron transfer through the capacitor[28,29]. Each quantum dot is coupled by tunneling barriers to different electronic reservoirs considered at local equilibrium. One of them, that we denote as s, allows charge transport between two terminals at the same temperature but different voltages. The other one, g, which is coupled only to one reservoir at a different temperature, supports no stationary charge but heat current. In previous work, we have shown that such geometry is able to generate a charge current in the unbiased two terminal conductor by converting the heat flowing though the gate quantum dot[9,30]. Energy

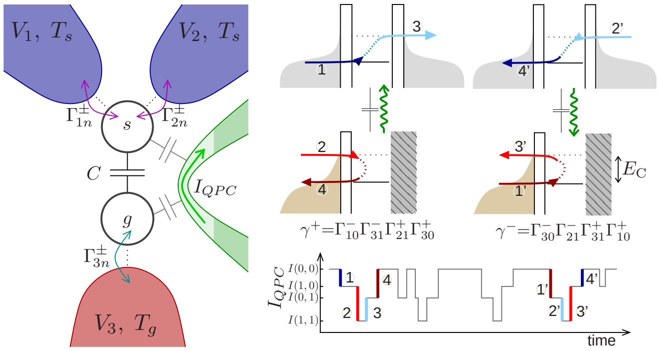

FIG. 1: Proposed scheme for heat detection. Two capacitively coupled quantum dots are connected to three terminals. One quantum dot (s) supports charge transport between two terminals. The other one (g) leads to heat transfer from a hot reservoir. A quantum point contact is asymmetrically coupled to both dots serving as a four state charge detector. Time resolved cycles involving all the states, 1→2→3→4, represent the transfer of one quantum of heat, E_C, from the hot to the cold conductor. The reversed sequence, $1'\rightarrow2'\rightarrow3'\rightarrow4'$, takes heat from the cold to the hot reservoir.

dependent tunneling barriers provide the necessary symmetry breaking[31]. The perpendicular directions of heat and charge currents is an important issue for energy harvesting from an environment. Related effects have been predicted in a variety of configurations, when the third hot terminal consists of a phonon bath[32,33], the electromagnetic environment[34], incoherent radiation[35] or a spin insulator[11]. Recently, current generation from absorption of external radiation has been detected in periodic semiconductor heterostructures[36,37], following ideas by one of us[38,39] and van Kampen[40].

Placing a QPC close to the quantum dots allows to determine the charge occupation of the system. The transparency of the constriction is affected by the electrostatic coupling to the charge of the quantum dots. In general, the coupling of the QPC to each quantum dot will be different, strongly depending of their distance. This makes the current flowing through the QPC sensitive to the different charging states. We emphasize that similar arrangements have allowed directional charge counting[15,26] or the detection of quantum operations[41] in double quantum dot systems. Alternatively, more complex setups of two QPCs, each one coupled to one quantum dot, can be used[42]. The backaction of the detector on the system charge states can be tuned to be negligible.

We propose detection of energy flows based on *state resolved* charge counting. We consider a QPC detector with no backaction on the system. In our case, we will focus on a Coulomb blockade regime where each quantum dot is described by a single discrete level that can be occupied by up to one electron. That reduces our configuration to a four state basis: $(N_s,N_g)=\{(0,0),(1,0),(0,1),(1,1)\}$. The generalization to cases with several levels is straightforward. Up to sequential tunneling, three states only are not enough to induce correlations between the two conductors[31]. Due to level discretization, interdot energy flows occur in quanta, $E_C=2q^2/\tilde{C}$, defined in terms of the geometrical capacitance of the coupled system, $\tilde{C}$[9]. Sequences can be identified in the time trace of the current through the QPC, (0,0)→(1,0)→(1,1)→(0,1)→(0,0), that represent the transfer of an energy E_C from the hot gate to the conductor, as sketched in Fig. 1. The reversed trajectory transfers energy from the cold to the hot system.

II. MODEL

We are interested in a system supporting non parallel electronic charge and heat currents. The three terminal device described above is the minimal model of this characteristics. Heat is transferred between the two dots by electron-electron interaction only. At sufficiently low temperatures, phononic heat transport can be neglected. Coulomb interaction is modeled by the capacitances associated to the tunneling barriers, C_l and the interdot coupling, C. In a self-consistent treatment, they define the charging energies, $U_{\alpha,n}(\{V_l\})$, of quantum dot α when the occupation of the other dot is $n=0,1$[9]. The quantum of transferred energy is given by the interdot charging energy, $E_C=U_{\alpha,1}-U_{\alpha,0}=2q^2/\tilde{C}$, with the effective capacitance $\tilde{C}=(C_{\Sigma s}C_{\Sigma g}-C^2)/C$, $C_{\Sigma s}=C_1+C_2+C$, and $C_{\Sigma g}=C_g+C$. The three terminals are assumed to be at thermal equilibrium with voltage V_l and temperature T_l. We will focus on the case that the two terminals of the conductor are at the same temperature, $T_1=T_2=T_s$ but can be at different voltages.

A. Master equation

The dynamics of our system can be described by a master equation for the reduced density matrix of the quantum dot system, $\boldsymbol{\rho}$. We consider the sequential regime, where only diagonal elements of the density matrix are important[43,44]. Processes in which an electron tunnels out (+) or into (−) a quantum dot through junction l with $n=0,1$ electrons in the other quantum dot are described by the tunneling rates $\Gamma_{ln}^{\pm}$. They are calculated by Fermi's golden rule, giving: $\Gamma_{ln}^{-}=\Gamma_{ln}f[(E_{\alpha n}-qV_l)\beta_l]$, $\Gamma_{ln}^{+}=\Gamma_{ln}-\Gamma_{ln}^{-}$, with $\beta_l=(kT_l)^{-1}$, $E_{\alpha n}=\varepsilon_\alpha+U_{\alpha n}$, being $f(x)=(1+e^x)^{-1}$ the Fermi function. ε_α is the bare energy of the discrete level in quantum dot α. The rates Γ_{ln} are in general energy dependent[45–47]. In particular, they depend on the charge occupation of the coupled dot. In the regime $kT\gg\Gamma_{ln}$, broadening of the energy levels can be neglected. Written in matrix form, such that $\boldsymbol{\rho}=(\rho_{00},\rho_{10},\rho_{01},\rho_{11})$, the master equation reads $\dot{\boldsymbol{\rho}}=\boldsymbol{\mathcal{M}}\boldsymbol{\rho}$, with

$$\boldsymbol{\mathcal{M}}=\begin{pmatrix} -\Gamma_{s0}^{-}-\Gamma_{g0}^{-} & \Gamma_{s0}^{+} & \Gamma_{g0}^{+} & 0 \\ \Gamma_{s0}^{-} & -\Gamma_{s0}^{+}-\Gamma_{g1}^{-} & 0 & \Gamma_{g1}^{+} \\ \Gamma_{g0}^{-} & 0 & -\Gamma_{s1}^{-}-\Gamma_{g0}^{+} & \Gamma_{s1}^{+} \\ 0 & \Gamma_{g1}^{-} & \Gamma_{s1}^{-} & -\Gamma_{s1}^{+}-\Gamma_{g1}^{+} \end{pmatrix} \quad (1)$$

and $\Gamma_{sn}^{\pm}=\Gamma_{1n}^{\pm}+\Gamma_{2n}^{\pm}$. For convenience, we can separate $\boldsymbol{\mathcal{M}}$ into diagonal and non diagonal terms: $\boldsymbol{\mathcal{M}}=\boldsymbol{\mathcal{M}_D}+\sum_{l,n,k}\boldsymbol{\mathcal{J}_{ln}^{k}}$. The matrices $\boldsymbol{\mathcal{J}_{ln}^{k}}$ correspond to those jumps described by tunneling rates Γ_{ln}^{k}. They allow one to express the charge, energy and heat stationary currents, $I_{\rm C,l}$, $I_{\rm E,l}$ and $I_{\rm H,l}$, respectively, in a compact form:

$$\langle I_{a,l}\rangle=\sum_n \mathrm{tr}[\Theta_{ln}^{a}\left(\boldsymbol{\mathcal{J}_{ln}^{+}}-\boldsymbol{\mathcal{J}_{ln}^{-}}\right)\bar{\boldsymbol{\rho}}], \quad (2)$$

where $\Theta_{l,n}^{a}$ represents the transported amount in each tunneling event: $\Theta_{ln}^{\rm C}=q$ (for charge), $\Theta_{ln}^{\rm E}=E_{\alpha n}$ (for energy) and $\Theta_{ln}^{\rm H}=E_{\alpha n}-qV_l$ (for heat). Note that they are related by: $I_{\rm H,l}=I_{\rm E,l}-I_{\rm C,l}V_l$. We obtain $\bar{\boldsymbol{\rho}}$ from the steady state solution given by $\boldsymbol{\mathcal{M}}\bar{\boldsymbol{\rho}}=0$. From charge conservation, we know that $I_{\rm C,g}=0$ and $I_{\rm C,s}=I_{\rm C,2}=-I_{\rm C,1}$, which allows us to define the total charge current flowing through the conductor, $I_{\rm C,s}$. The state resolved charged currents, $\langle I_{ln}\rangle$, are given by the terms inside the sum in Eq. (2).

III. COUNTING STATISTICS AND FLUCTUATION THEOREMS

Briefly, in the master equation formalism the cumulant generating function of the counting statistics is obtained from the eigenvalue closest to zero of the matrix $\boldsymbol{\mathcal{M}}_{\boldsymbol{\chi}}$, as determined from $\boldsymbol{\mathcal{M}}$ when introducing the counting fields $\chi_{a,l}$ multiplying the corresponding off diagonal elements, $\boldsymbol{\mathcal{J}}_{\boldsymbol{ln}}^{\boldsymbol{k}}$, with $z_{a,ln}^{k}{=}e^{ik\Theta_{l,n}^{a}\chi_{a,l}}$[48]. Different counting fields, $\boldsymbol{\chi_a}$, with $a = \mathrm{C}, \mathrm{E}, \mathrm{H}$, give rise to the statistics of the different charge, energy and heat currents. Doing so, and noticing that $\Gamma_{ln}^{+} = e^{\Theta_{ln}^{\mathrm{H}}\beta_l}\Gamma_{ln}^{-}$, which translates to

$$\mathcal{J}_{ln}^{+} = e^{\Theta_{ln}^{\mathrm{H}}\beta_l}(\mathcal{J}_{ln}^{-})^{T}, \tag{3}$$

one can easily verify the symmetries of the characteristic polynomial $\det|\boldsymbol{\mathcal{M}}_{\boldsymbol{\chi}}{-}\lambda\mathbb{1}|{=}0$. For uniform temperatures, $T_l{=}T, \forall l$, one obtains the fluctuation theorem for charge transport:

$$\mathcal{F}(i\boldsymbol{\chi}_{\mathbf{C}}){=}\mathcal{F}(-i\boldsymbol{\chi}_{\mathbf{C}} + \boldsymbol{A}_{\mathbf{C}}), \tag{4}$$

with the affinities $A_{\mathrm{C,l}}{=}V_l\beta_l$[19]. At zero applied voltage, one expects that detailed balance restores equilibrium. However, a finite charge current flows in the presence of hot spots[9,30]. This apparent broken detailed balance is restored when considering the energy flows as well by introducing the energy counting fields. For that one has to include the product $z_{\mathrm{C,ln}}^{k}z_{\mathrm{E,ln}}^{k}$ into the master equation. By doing so, the combined charge and energy cumulant generating function is invariant under the transformation $\{i\boldsymbol{\chi}_{\mathbf{C}}, i\boldsymbol{\chi}_{\mathbf{E}}\} \rightarrow \{-i\boldsymbol{\chi}_{\mathbf{C}}{+}\boldsymbol{A}_{\mathbf{C}}, -i\boldsymbol{\chi}_{\mathbf{E}}{-}\boldsymbol{A}_{\mathbf{H}}\}$, with the energy affinities $A_{\mathrm{H,l}}{=}\beta_l$[27]. Notice that the local detailed balance condition expressed in Eq. (3) involves the heat carried by electrons in the tunneling processes. Thus a more compact form of the fluctuation theorem can be written in terms of heat currents —which we showed to be related to charge and energy currents— when considering the heat counting fields $z_{\mathrm{H,l}}^{k}$:

$$\mathcal{F}(i\boldsymbol{\chi}_{\mathbf{H}}){=}\mathcal{F}(-i\boldsymbol{\chi}_{\mathbf{H}}{-}\boldsymbol{A}_{\mathbf{H}}), \tag{5}$$

valid in the presence of both voltage and temperature gradients. As mentioned above, a way to gather information about the heat transfer is by state resolved counting statistics, once the energies $\Theta_{l,n}^{\mathrm{E}}$ are known. In our configuration, this information can be accessed experimentally. Furthermore, if we are interested in the heat transferred between the two conductors, only the difference $\Theta_{l,1}^{\mathrm{E}}{-}\Theta_{l,0}^{\mathrm{E}}{=}E_C$ becomes relevant.

A. State resolved fluctuation relations

If one is able to distinguish what state of the quantum dot system is involved in the tunneling of the detected charges, the same information is given by state resolved counting. This is the same as introducing $z_{ln}^{k}{=}\exp[ik\zeta_{ln}]$ multiplying the corresponding rates Γ_{ln}^{k} in the off-diagonal elements of the matrix $\boldsymbol{\mathcal{M}}$. N_{ln} denotes the number of transferred charges through terminal l and from state n, and ζ_{ln} are the level resolved particle counting fields. Note that $N_l{=}\sum_n N_{ln}$. The explicit level dependence of local deltailed balance conditions in Eq. (3) provides the fulfillment of the state resolved fluctuation relation:

$$\mathcal{F}(i\boldsymbol{\zeta}){=}\mathcal{F}(-i\boldsymbol{\zeta}{-}\tilde{\boldsymbol{A}}), \tag{6}$$

where $\boldsymbol{\zeta}$ and $\tilde{A}_{l,n}{=}\Theta_{l,n}^{\mathrm{H}}\beta_l$ are the state resolved charge counting fields and affinities, respectively. The dimension of the vectors $\boldsymbol{\zeta}$ and $\tilde{\boldsymbol{A}}$ is the number of terminals times the number of states. In contrast to Eq. (4), the relation shown in Eq. (6) is valid also in the presence of temperature gradients. As a drawback, it is no longer universal but depends on the internal configuration of the system — in particular, on gate voltages. However, we stress that, in a self-consistent treatment, $\Theta_{l,n}^{\mathrm{H}}{=}E_{\alpha,n}(\{V_m\}){-}qV_l$ depends only on differences of voltages, so Eq. (6) is gauge invariant.

In a recent work, Krause *et al.*[49] showed that state resolved counting of electrons allows fluctuation relations to be written when the statistics of energy dissipated is also measurable. That is not the case for phonons. In our setup, the energy absorbed by a conductor is only due to electron-electron interactions and can be treated in the same footing as the particle currents, as we show below. State resolved counting of electrons therefore provides the required information about the energy transfers.

Our system allows for such state resolved counting. The quantity of interest is the heat flowing through the gate. This is independent of the number of levels of each dot. The relevant index is given by the charge occupation. For quantum dots that permit up to one electron, $n{=}1, 0$ labels the charge occupation of the dot that is not involved in the tunneling event. The conductor absorbs a quantum of energy E_C from the gate when an electron enters the gate dot occupying the state (1,1) and leaves it from state (0,1) (after the electron occupying the conductor dot has been transferred carrying the extra energy to any lead). Thus, the amount of energy transferred to the gate lead is proportional to the difference of the number of electrons that have tunneled from the two states (1,1) and (0,1):

$$\tilde{E}_g{=}E_C(N_{g1}{-}N_{g0}). \tag{7}$$

This equation relates the transferred heat statistics to the charge fluctuations in the gate, which can be measured in a state dependent detector as the one shown in Fig. 1.

Charge and energy conservation can be written in terms of state resolved counting: $\sum_{l\in s}N_l{=}N_g{=}0$ and $\sum_{l\in s}(N_{l,1}{-}N_{l,0}){=}N_{g,1}{-}N_{g,0}$, respectively. They provide additional symmetries of the cumulant generating function expressed as shifts of the counting fields. If we separate the contributions from each conductor, system and gate, $\boldsymbol{\zeta}{=}(\boldsymbol{\zeta_s}, \boldsymbol{\zeta_g})$, we obtain:

$$\mathcal{F}(i\boldsymbol{\zeta_s}, i\boldsymbol{\zeta_g}){=}\mathcal{F}(i\boldsymbol{\zeta_s} + a, i\boldsymbol{\zeta_g} + b), \tag{8}$$

for arbitrary parameters a and b. If, on the other hand, we separate particles tunneling at different energies, $\boldsymbol{\zeta_l}=(\boldsymbol{\zeta_{l0}},\boldsymbol{\zeta_{l1}})$:

$$\begin{aligned}&\mathcal{F}(i\boldsymbol{\zeta_{s0}},i\boldsymbol{\zeta_{s1}},i\boldsymbol{\zeta_{g0}},i\boldsymbol{\zeta_{g1}})=\\&\mathcal{F}(i\boldsymbol{\zeta_{s0}}-a,i\boldsymbol{\zeta_{s1}}-b,i\boldsymbol{\zeta_{g0}}+b,i\boldsymbol{\zeta_{g1}}+a).\end{aligned}\tag{9}$$

The dimension of vectors $\boldsymbol{\zeta_{sn}}$ and $\boldsymbol{\zeta_{gn}}$ is given by the number of levels in each conductor times the number of terminals to which it is connected. Eqs. (6) and (9) lead to an incomplete fluctuation theorem when only electrons flowing through the conductor are measured[49]:

$$\mathcal{F}(i\boldsymbol{\zeta_{sn}})=\mathcal{F}(-i\boldsymbol{\zeta_{sn}}-\tilde{\boldsymbol{A}}_{\boldsymbol{sn}}-\tilde{\boldsymbol{A}}_{\boldsymbol{g\bar{n}}}).\tag{10}$$

Note that the system and gate affinities are taken at different occupations, $\bar{n}$=not(n). It can be useful in cases where the QPC is not able to distinguish the states (0,0) and (0,1).

The state resolved cumulant generating function is defined in terms of the probability to detect $\mathbf{N}$ transferred electrons during a period of time, t: $\mathcal{F}(i\boldsymbol{\zeta})=\ln\sum_{\boldsymbol{N}}P(\boldsymbol{N},t)e^{-i\boldsymbol{N}\boldsymbol{\zeta}}$. For later convenience, the charge currents will be written in terms of the number of electrons transferred in a given time: $I_{ln}=qN_{ln}/t$. Then, in the long time limit, Eq. (10) can be expressed in terms of the probability to measure a given current configuration, $\boldsymbol{I_{sn}}$, in the conductor[52]:

$$\frac{1}{t}\ln\frac{P(\boldsymbol{I_{sn}})}{P(-\boldsymbol{I_{sn}})}=\sum_{l\in s,n}I_{ln}(\Theta^{\rm H}_{l,n}-\Theta^{\rm H}_{g,\bar{n}}).\tag{11}$$

In the case of interest here where the two terminals of the conductor s are at the same temperature, the previous expression can be nicely rewritten in terms of the total charge current, $I_{\rm C,s}=q\sum_n N_{2n}/t$, and the amount of energy absorbed from the gate, $I_{\rm H,g}=\tilde{E}_g/t$, expressed in terms of particle flows in the conductor, cf. Eq. (7):

$$\frac{1}{t}\ln\frac{P(\boldsymbol{I_{sn}})}{P(-\boldsymbol{I_{sn}})}=I_{\rm C,s}(V_1-V_2)\beta_s-I_{\rm H,g}(\beta_g-\beta_s)/2.\tag{12}$$

It resembles fluctuation theorems for thermoelectric transport that separate thermal and electric forces[27,49–51]. However, Eq. (12) is configuration dependent: the right hand side depends on state resolved currents through $I_{\rm H,g}$. For instance, it is affected by gate voltages. For a single level quantum dot, it reads: $I_{\rm H,g}=2E_C(I_{\rm C,s}-I_{11}+I_{20})$, where the last two terms represent the difference of state resolved currents I_{ln} flowing through the different leads (l=1, 2) of the conductor at the different charge occupations (n=1, 0) of the gate quantum dot.

An illustration of the previous expression is plotted in Fig. 2. We denote the right hand side of Eq. (12) with ξ. Remember that $I_{\rm H,g}$ can be written in terms of charge currents. Remarkably, in asymmetric configurations that manifest noise induced transport, $\langle\xi\rangle$ does not vanish even if the total current, $\langle I_{\rm C,s}\rangle$, does at a certain stall potential. Though at that voltage no net charge currents flow, heat flowing through the gate drives the system out of equilibrium. Detailed balance is restored only at the optimal converter configuration, cf. Eq. (13) below.

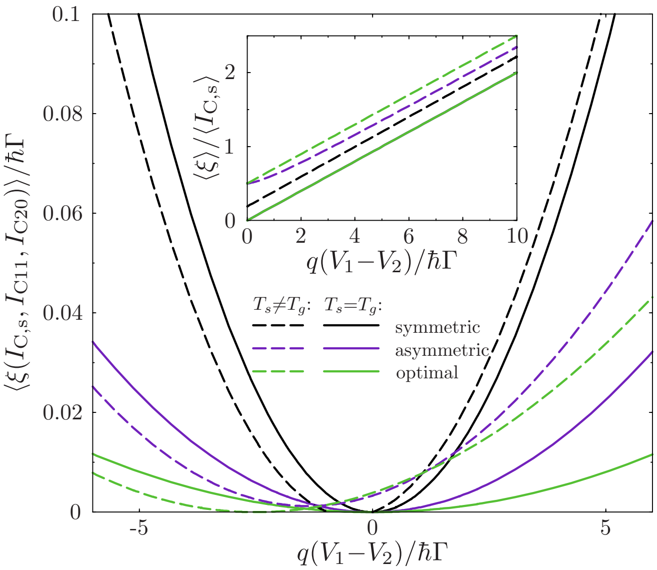

FIG. 2: Fluctuation relation. We plot the right hand side of Eq. (12) written in terms of mean charge currents: $\langle\xi\rangle=\langle I_{\rm C}\rangle(V_1-V_2)\beta_s-E_C(\langle I_{\rm C,s}\rangle-\langle I_{11}\rangle+\langle I_{20}\rangle)(\beta_g-\beta_s)$, as a function of the bias voltage applied to the conductor. The inset shows the same curves normalized to the total charge current, $\langle I_{\rm C,s}\rangle$, for clarity. Different tunneling rate configurations are shown for homogeneous (T_s=T_g) and inhomogeneous ($T_s\neq T_g$) temperatures: "symmetric"(Γ_{ln}=Γ, $\forall\{l,n\}$), "asymmetric"(Γ_{ln}=Γ, except Γ_{11}=Γ_{20}=$\Gamma/10$), and "optimal"(Γ_{ln}=Γ, except Γ_{11}=Γ_{20}=0). The temperature of the conductor is kept kT_s=5$\hbar\Gamma$, while the gate is heatted to kT_g=10$\hbar\Gamma$ in the inhomogeneous case. The presence of a hot spot generates a shift of the minimum. For asymmetric configurations, it does not cross the origin except for the optimal case, in which it goes to zero at the stall potential of Eq. (15).

Optimal heat to charge conversion occurs in particular cases where the tunneling events (0,0) ↔ (1,0) and (0,1) ↔ (1,1) can only take place through different terminals of the conductor[9]. For instance, if $\Gamma_{11}\ll\Gamma_{10}$ and $\Gamma_{20}\ll\Gamma_{21}$, so $I_{11},I_{20}\to0$. Then, a universal relation holds:

$$\frac{1}{t}\ln\frac{P(I_{\rm C,s})}{P(-I_{\rm C,s})}=I_{\rm C,s}[(V_1-V_2)\beta_s-E_C(\beta_g-\beta_s)].\tag{13}$$

The involved cycles are illustrated in Fig. 1. At this configuration, a charge q is transported across the conductor for each quantum of heat E_C that is exchanged between the two systems, so $I_{\rm C,s}/q=I_{\rm H,g}/E_C$. This implies that $I_{\rm C,s}$ and $I_{\rm H,g}$ are maximally correlated, i.e. $\langle I_{\rm C,s}I_{\rm H,g}\rangle=\langle I_{\rm C,s}\rangle\langle I_{\rm H,g}\rangle$, and all their cumulants coincide.

Note that a related expression can be obtained using the relation of rates for the cycle that transfers an energy E_C to the conductor, $\gamma^+=\Gamma^-_{10}\Gamma^-_{31}\Gamma^+_{21}\Gamma^+_{30}$, and its reversed

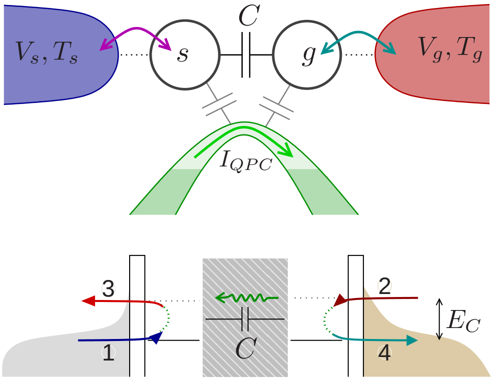

FIG. 3: Heat diode in a two terminal configuration. Here, no charge but only heat transport takes place through the capacitor.

sequence, $\gamma^-{=}\Gamma_{30}^-\Gamma_{21}^-\Gamma_{31}^+\Gamma_{10}^+$, which gives:

$$\frac{\gamma^+}{\gamma^-}{=}\exp[q(V_1{-}V_2)\beta_s{+}E_C(\beta_s{-}\beta_g)]. \tag{14}$$

The exponent in the right hand side of Eq. (14) is given by the entropy flux per cycle[53,54]. We can therefore interpret the right hand side of Eq. (13): it relates the entropy flux to the Joule heat in the conductor and heat absorbed from the gate. It also provides the condition for the stall potential

$$q(V_1{-}V_2){=}E_C\frac{\beta_g{-}\beta_s}{\beta_s}{=}{-}E_C\eta_C, \tag{15}$$

where a conversion efficiency approaching the Carnot limit is predicted[9].

IV. PURE HEAT TRANSPORT

As discussed above, charge current statistics suffer deviations from a universal behaviour in the presence of thermal gradients —unless one has access to the whole level dependent transferences, distinguishing the involved terminal as well. On the other hand, an applied voltage to the conductor prevents a fluctuation relation in terms of the gate charge only. One can avoid such difficulties by considering a two terminal system where no stationary charge current will flow[13]. A schematic representation of such a system with the QPC detector added is shown in Fig. 3. Note that in this configuration, heat and energy currents coincide, $I_{\mathrm{H,l}}{=}I_{\mathrm{E,l}}{=}E_C I_{l1}/q$, and therefore are conserved: $\sum_l I_{\mathrm{H,l}}{=}\sum_l I_{\mathrm{E,l}}{=}0$.

In this case, the validity of the fluctuation theorem can be verified by detecting the statistics of charge transferred from a given energy. The constraints introduced by charge conservation in each conductor ($N_{l0}{=}{-}N_{l1}$) and energy conservation ($N_{s1}{=}{-}N_{g0}$) permits to write separate relations for particles emitted through any state or terminal, N_{ln}. For example, one can simply count the number of electrons N_{sn} emitted to the cold system conditioned on the hot dot containing n electrons. The corresponding cumulant generating function obeys the symmetry:

$$\mathcal{F}(i\zeta_{sn}){=}\mathcal{F}({-}i\zeta_{sn}{+}E_C\,(\beta_g{-}\beta_s)). \tag{16}$$

For particles emitted through the gate terminal, replace $s \leftrightarrow g$ in the previous expression. No gate voltage dependence enters Eq. (16).

V. CONCLUSIONS

To summarize, we propose a mechanism to detect the statistics of electronic heat currents in Coulomb blockaded quantum dot systems. Multilevel charge detection by means of a side coupled quantum point contact allows to count the transfer of discrete energy E_C. The same scheme permits to investigate deviations of charge flow statistics in the presence of hot spots, manifested in non universal fluctuation relations. We investigate a three terminal heat to charge converter where noise induced transport avoids detailed balance of charge flows. Only for an optimal configuration when the absorption of a quantum of heat E_C leads to the transfer of a charge q across the conductor, can a fluctuation theorem for total charge flow be written. In a two terminal device with no net charge currents, state resolved charge counting statistics fulfill the fluctuation theorem as obtained for heat currents. All our results can be probed within present experimental technology.

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